

**PATENT APPLICATION**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of

Docket No: Q76253

Naoki OYANAGI

Appln. No.: 10/560,745

Group Art Unit: 1792

Confirmation No.: 1691

Examiner: Felisa Carla HITESHEW

Filed: December 15, 2005

For: METHOD FOR GROWTH OF SILICON CARBIDE SINGLE CRYSTAL, SILICON  
CARBIDE SEED CRYSTAL, AND SILICON CARBIDE SINGLE CRYSTAL

**AMENDMENT UNDER 37 C.F.R. § 1.111**

**MAIL STOP AMENDMENT**

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Sir:

In response to the Office Action dated March 13, 2008, please amend the above-  
identified application as follows on the accompanying pages.

**TABLE OF CONTENTS**

AMENDMENTS TO THE CLAIMS .....2

REMARKS ..... 5